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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Re: U.S. National Filing under )  
35 U.S.C. §371 of International )  
Application No. PCT/DE00/03293 )      PATENT  
                                      )  
                                      )  
German Title: Mehrwertiger Magnetoresistiver )  
Schreib/Lese-Speicher sowie Verfahren )  
zum Beschreiben eines solchen Speichers )  
                                      )  
                                      )  
English Translation: Multivalue Magnetoresistive Read/Write )  
Memory and Method of Writing to and )  
Reading from Such a Memory )  
                                      )  
Applicant: Infineon Technologies, AG )  
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Inventors: Thewes, Roland )  
Schwarzl, Siegfried )  
Weber, Werner )

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Honorable Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Sir:

**PRELIMINARY AMENDMENT**

In the above-entitled patent application, please amend the application as follows:

In the Claims

Please amend Claim No. 1 as follows:

1         1. (amended) A magnetoresistive read/write memory, with a plurality of  
2         multivalue storage cells [(11)], each storage cell [(11)] having two intersecting electric  
3         conductors [(12, 13)] and a layer system comprising magnetic layers located at the  
4         intersection of [the] said electric conductors [(12, 13)], wherein [the] said layer system is  
5         designed as a multilayer system [(30; 40)] with two or more magnetic layers [(31, 32;  
6         41-45)], at least two, but a maximum of all [the] said magnetic layers [(31, 32; 41-45)]  
7         having a magnetization direction [(33, 34; 46-50)] that can be set independently of one  
8         another, [the] said magnetization direction [(33, 34; 46-50)] in [the] said individual layers  
9         [(31, 32; 41-45)] [is] being changed [or can be changed] by the electric current flowing